

**IN THE CLAIMS:**

Claims 1-13 (Canceled)

Claim 14 (Original) A method of selective removing amorphous Si as compared to SiGe comprising the steps of:

etching a structure containing exposed surfaces of amorphous Si and SiGe with an aqueous solution of HF to remove oxide from the exposed surfaces;

rinsing the aqueous solution of HF from the surfaces with deionized water to form an oxide on said SiGe exposed surfaces;

etching the exposed amorphous Si surfaces with an aqueous  $\text{NH}_4\text{OH}$  to selectively remove the amorphous Si at a faster rate than the SiGe;

rinsing with deionized water; and

drying with a monohydric alcohol.

Claim 15 (Original) The method of Claim 14 wherein the rate of amorphous Si removal is about 25 /min or greater and the rate of SiGe removal is about 4 Å/min or less.

Claim 16 (Original) The method of Claim 14 wherein the monohydric alcohol is isopropanol.

Claim 17 (Original) The method of Claim 14 wherein the aqueous solution of HF comprises a ratio of  $\text{H}_2\text{O}:\text{HF}$  of from about 1:1 to about 500:1 and the HF etching occurs at a temperature of from about 23°C to about 60°C.

Claim 18 (Original) The method of Claim 14 wherein the aqueous solution of  $\text{NH}_4\text{OH}$  comprises a ratio of  $\text{H}_2\text{O}:\text{NH}_4\text{OH}$  of from about 3:1 to about 500:1 and the  $\text{NH}_4\text{OH}$  etching occurs at a temperature of from about 23°C to about 65°C.

Claim 19 (Original) The method of Claim 14 the steps of  $\text{NH}_4\text{OH}$  etching and subsequent rinsing are repeated any number of times.

Claim 20 (Original) The method of Claim 19 wherein multiple  $\text{NH}_4\text{OH}$  etching steps are employed in which at least one of the multiple  $\text{NH}_4\text{OH}$  etching occurs without a rinsing step.